

Si photodiode array

S4111/S4114 series

16, 35, 46 element Si photodiode array for UV to NIR



S4111/S4114 series are Si photodiode linear array mounted in ceramic DIPs (Dual Inline Packages). These photodiode arrays are primarily developed for low-light-level detection such as spectrophotometry, and cover a wide spectral range from UV to near infrared light. Since all elements can be used with a reverse bias for charge storage readout, S4111/S4114 series are able to detect low level light with high sensitivity. Cross-talk between elements is minimized to maintain signal purity. Special filters can be attached as the input window.

Features

- Large active area
- Low cross-talk
- Wide spectral response range
- High UV sensitivity
- Wide linearity
- S4111 series: Enhanced infrared sensitivity, low dark current
- S4114 series: Low terminal capacitance, high-speed response

Applications

- Multichannel spectrophotometers
- Color analyzers
- Light spectrum analyzers
- Light position detection

General ratings / Absolute maximum ratings

Type No.	Dimensional outline/ Window material *	Package (mm)	Active area (per 1 element)		Between elements measure (mm)	Between elements pitch (mm)	Number of elements	Absolute maximum ratings				
			Size (mm)	Effective area (mm ²)				Reverse voltage VR Max. (V)	Operating temperature Topr (°C)	Storage temperature Tstg (°C)		
S4111-16Q	①/Q	18 pin DIP	1.45 × 0.9	1.305	0.1	1.0	16	15	-20 to +60	-20 to +80		
S4111-16R	②/R											
S4111-35Q	③/Q	40 pin DIP	4.4 × 0.9	3.96							35	
S4111-46Q	④/Q	48 pin DIP										46
S4114-35Q	③/Q	40 pin DIP										
S4114-46Q	④/Q	48 pin DIP										46

Electrical and optical characteristics (Typ. Ta=25 °C, per 1 element, unless otherwise noted)

Type No.	Spectral response range λ (nm)	Peak sensitivity wavelength λp (nm)	Photo sensitivity S			Dark current Id Max.		Shunt resistance Rsh VR=10 mV		Terminal capacitance Ct		Rise time tr RL=1 kΩ λ=655 nm		NEP λ=λp	
			λp (A/W)	200 nm (A/W)	633 nm (A/W)	VR=10 mV (pA)	VR=10 V (pA)	Min (GΩ)	Typ. (GΩ)	VR=0 V (pF)	VR=10 V (pF)	VR=0 V (μs)	VR=10 V (μs)	VR=0 V (W/Hz ^{1/2})	VR=10 V (W/Hz ^{1/2})
S4111-16Q	190 to 1100	960	0.58	0.08	0.43	5	25	2.0	250	200	50	0.5	0.1	4.4 × 10 ⁻¹⁶	1.7 × 10 ⁻¹⁵
S4111-16R	320 to 1100			-	0.39										
S4111-35Q	190 to 1100	800	0.50	0.08	0.43	10	50	1.0	30	550	120	1.2	0.3	1.3 × 10 ⁻¹⁵	3.1 × 10 ⁻¹⁵
S4111-46Q															
S4114-35Q	190 to 1000	800	0.50	0.08	0.43	60	300	0.15	2	35	20	0.1	0.05	5.7 × 10 ⁻¹⁵	8.0 × 10 ⁻¹⁵
S4114-46Q															

* Window material R: resin coating, Q: quartz glass

Spectral response

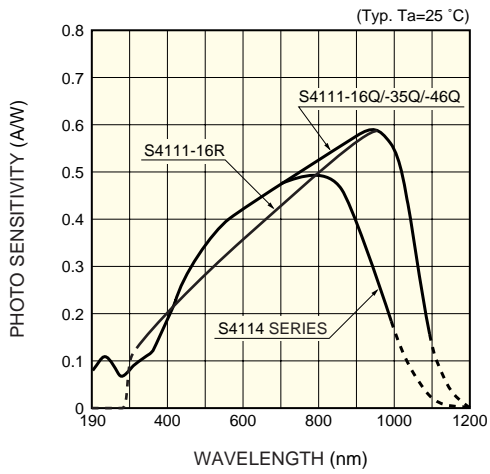
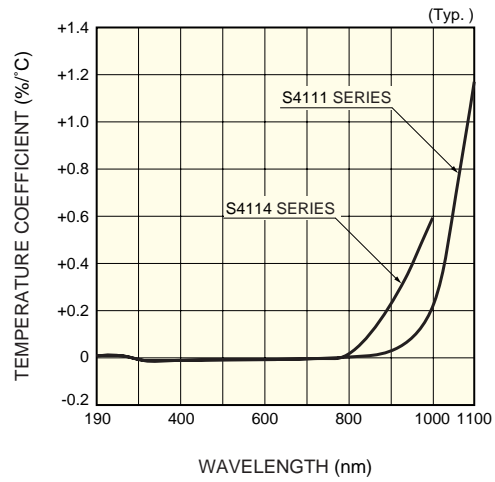
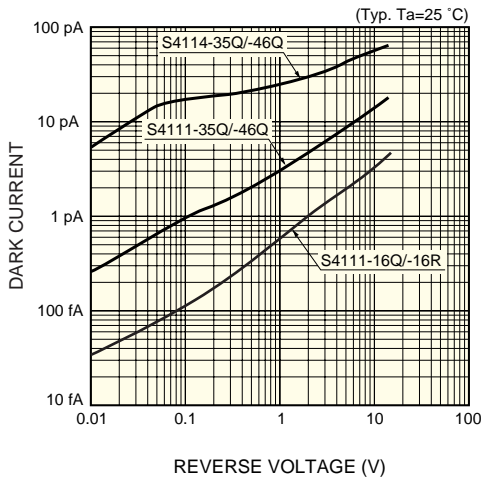


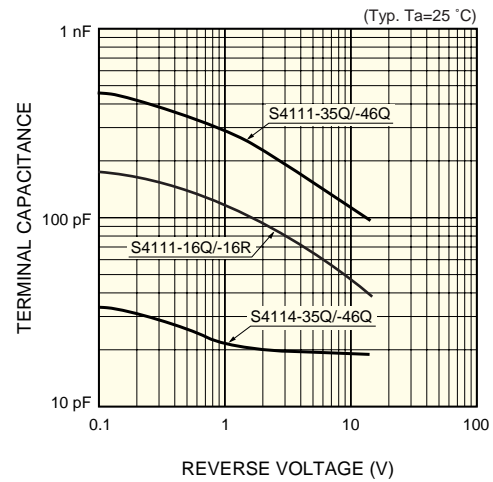
Photo sensitivity temperature characteristics



Dark current vs. reverse voltage

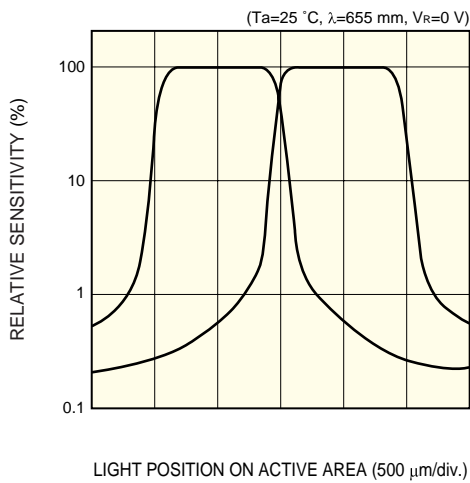


Terminal capacitance vs. reverse voltage

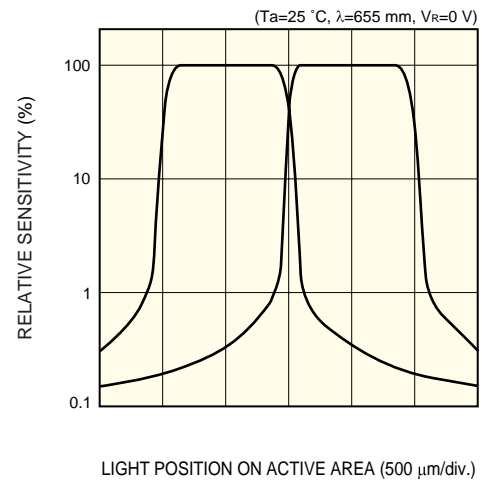


Example of cross-talk

S4111 series

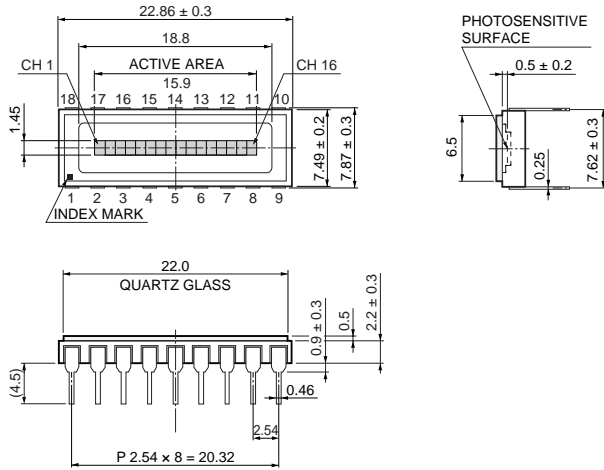


S4114 series



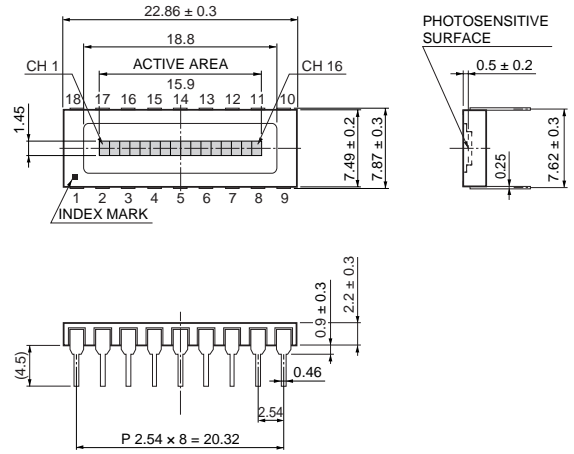
Dimensional outlines (unit: mm)

① S4111-16Q



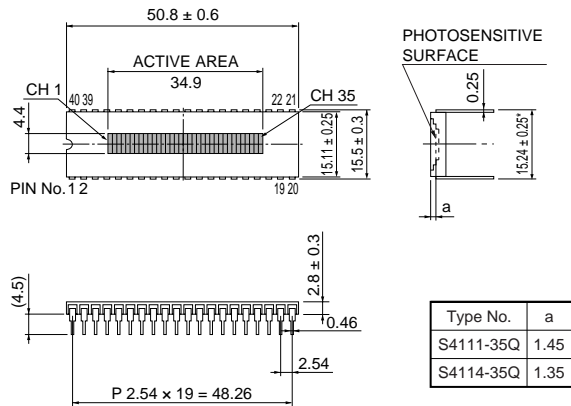
KMPDA0135EA

② S4111-16R



KMPDA0136EA

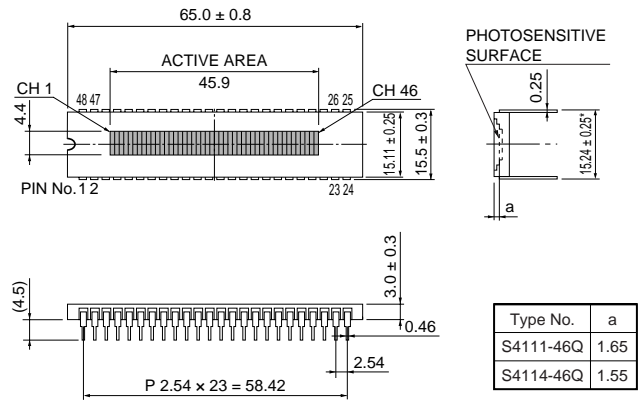
③ S4111-35Q, S4114-35Q



Type No.	a
S4111-35Q	1.45
S4114-35Q	1.35

KMPDA0019EC

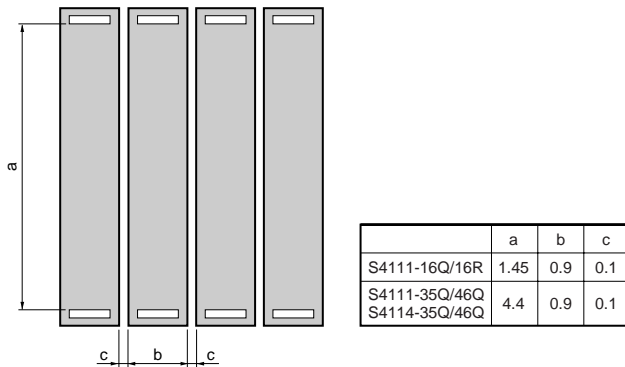
④ S4111-46Q, S4114-46Q



Type No.	a
S4111-46Q	1.65
S4114-46Q	1.55

KMPDA0021EC

Details of elements (for all types)



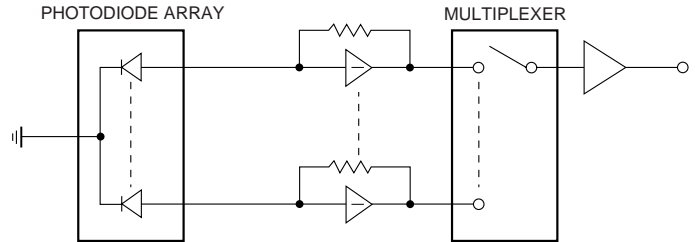
KMPDA0112EA

■ Pin connections

Pin No.	16-element type	35-element type	46-element type
1	KC	KC	KC
2	2	2	2
3	4	4	4
4	6	6	6
5	8	8	8
6	10	10	10
7	12	12	12
8	14	14	14
9	16	16	16
10	KC	18	18
11	15	NC	20
12	13	20	22
13	11	22	24
14	9	24	26
15	7	26	28
16	5	28	30
17	3	30	32
18	1	32	34
19		34	36
20		NC	38
21		KC	40
22		35	42
23		33	44
24		31	46
25		29	KC
26		27	45
27		25	43
28		23	41
29		21	39
30		19	37
31		17	35
32		15	33
33		13	31
34		11	29
35		9	27
36		7	25
37		5	23
38		3	21
39		1	19
40		NC	17
41			15
42			13
43			11
44			9
45			7
46			5
47			3
48			1

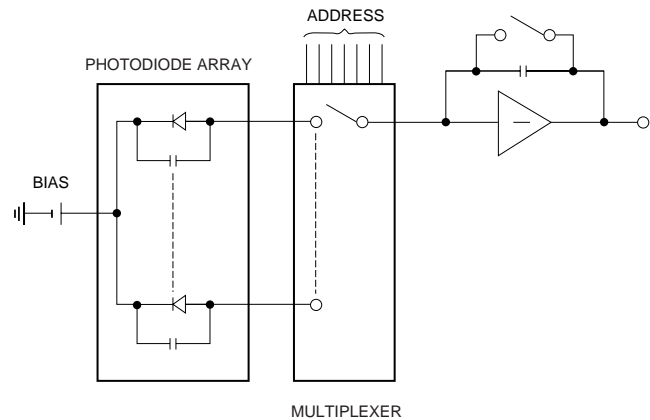
■ Operating circuits

① In the most generally used circuit, operational amplifiers are connected to each channel to read the output in real time. The output of an operational amplifier is of low impedance and thus can be easily multiplexed.



KMPDC0001EA

② In the charge storage readout method, the charge stored in the junction capacitance of each channel, which is proportional to the incident light intensity, can be read out in sequence by a multiplexer. With this method, reverse voltage must be applied to the photodiodes, so S4111 and S4114 series are suitable. One amplifier is sufficient but care should be taken regarding noise, dynamic range, etc.



KMPDC0002EA